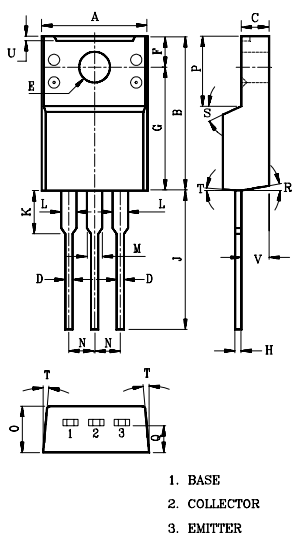
KTC4370A

EPITAXIAL PLANAR NPN TRANSISTOR

HIGH VOLTAGE APPLICATION.

FEATURES

- High Transition Frequency : f_T=100MHz(Typ.).
- Complementary to KTA1659A.



DIM	MILLIMETERS
A	10.30 MAX
B	15.30 MAX
C	2.70±0.30
D	0.85 MAX
E	φ3.20±0.20
F	3.00±0.30
G	12.30 MAX
H	0.75 MAX
J	13.60±0.50
K	3.90 MAX
L	1.20
M	1.30
N	2.54
O	4.50±0.20
P	6.80
Q	2.60±0.20
R	10°
S	25°
T	5°
U	0.5
V	2.60±0.15

1. BASE
2. COLLECTOR
3. EMITTER

TO-220IS

MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	180	V
Collector-Emitter Voltage	V_{CEO}	180	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	1.5	A
Base Current	I_B	0.15	A
Collector Power Dissipation (Tc=25℃)	P_C	20	W
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55~150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=160V, I_E=0	-	-	1.0	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=5V, I_C=0	-	-	1.0	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=10mA, I_B=0	180	-	-	V
DC Current Gain	h_{FE}(Note)	V_{CE}=5V, I_C=100mA	70	-	240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=500mA, I_B=50mA	-	-	1.5	V
Base-Emitter Voltage	V_{BE}	V_{CE}=5V, I_C=500mA	-	-	1.0	V
Transition Frequency	f_T	V_{CE}=10V, I_C=100mA	-	100	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1MHz	-	25	-	pF

Note: h_{FE} Classification O:70~140, Y:120~240